

- 30.3 *First-principles theoretical study of the stability and pressure-driven structural phase transitions of mercury chalcogenides*
59 Andrés Mujica (Spain)
- 30.4 *Surface photovoltage dynamics of Si (001)/SiO₂ and water saturated Si (001)-2x1 surface: laser pump-synchrotron radiation probe time-resolved photoemission study*
60 Debora Pierucci (France)
- 30.5 *Transport through p-doped Indium Arsenide nanowires*
61 Shivendra Upadhyay (Denmark)
- 30.6 *Delta doping effects in Lead Telluride and their implications on thermoelectric properties: Ab initio calculations*
62 Pablo D. Borges (United States)
- 30.7 *Type II InAs/GaSb infrared photodetectors for mid, long, and very long wavelength*
63 Wenquan Ma (People's Republic of China)
- 30.8 *Local Electron States Linked to the QuasiFermi Level*
64 Ludmila Ryabova (Russia)
- 30.9 *Nitrogen Ion Role on Photoluminescence Variation Observed in III-N-V Semiconductors*
65 Shogo Nonoguchi (Japan)
- 30.10 *Substantial temperature dependence of transverse electron g^* -factor in lead chalcogenide multi-quantum wells*
66 K Litvinenko (United Kingdom)
- 30.11 *Quasi-temperature-stable 1.3 μm emission from Flash Lamp Annealed GaAs*
67 Kun Gao (Germany)
- 30.12 *A new type of conductivity in semiconductors*
68 Sergey Obukhov (Russia)
- 30.13 *Tuning of the optical properties of In-rich $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($x=0.8-0.4$) alloys by light-ion irradiation at low energy*
69 Marta De Luca (Italy)

- 30.14 *Phonons in $\text{Hg}_{1-x}\text{Cd}_x\text{Se}$ Crystalline Alloys*
70 David Alejandro Miranda Mercado (Colombia)
- 30.15 *Raman scattering and low temperature photoluminescence of type II $\text{In}_{0.14}\text{Ga}_{0.86}\text{As}_{0.13}\text{Sb}_{0.87}\text{GaSb}$ heterostructure doped with Zinc grown by liquid phase epitaxy*
71 Joel Díaz-Reyes (Mexico)
- 30.16 *Critical Phenomena and Processes of Self-organization under Transition to Heavy Doping in Semiconductors*
72 Elena Rogacheva (Ukraine)
- 30.17 *First Principles Study on the Effect of the Position of Nitrogen Atoms on the Electronic Structure of GaAsN*
73 Kei Sakamoto (Japan)
- 30.18 *Oxygen-doping-induced Band-gap Reduction in II-VI Semiconductors; Comparison to III-V Systems*
74 Masato Ishikawa (Japan)

Session 31, 16:00–18:00, Poster area
Poster Carbon: Nanotubes and Graphenes I

- 31.1 *Structure of electron bands in one- and few-layer graphenes, bulk graphite and single-wall carbon nanotubes: resonant micro-Raman study*
75 Aleksandr Belyaev (Ukraine)
- 31.2 *On the Quantum Hall Effect in graphene*
76 Maxim Cheremisin (Russia)
- 31.3 *Angular Distribution of Field-Emitted (FE) Electrons from Vertically Aligned Carbon Nanotube Arrays and its use as cold field emitters for x-ray sources*
77 Michela Fratini (Italy)
- 31.4 *Identifying the Distinct Phases of THz Waves from K-valley Electrons in Graphite*
78 Young-Dahl Jho (South Korea)